

ABSTRACT OF THE DISCLOSURE

A method of manufacturing semiconductor device invented comprises a process of forming a gate electrode (5) having metallic silicide layer (3) on a semiconductor substrate, a process of decreasing boundaries of grains on the surface of said metallic silicide layer (3) at least a portion of which is exposed, and a process of forming spacers comprising oxide film (10) on the side wall of said gate electrode (5); in this order; so as to avoid the abnormal oxidation of said metallic silicide layer (3).